

Publication List

HUANG-MING LEE

A. 期刊論文

1. **H. M. Lee**, E. Y. Chang, S. H. Chen and C. Y. Chang, "New Nanometer T-Gate Fabricated by Thermally Reflowed Resist Technique", Jap. J. Appl. Phys., Vol. 41, No. 12B, 2002, pp. L1508-L1510.
2. **H. M. Lee**, T. H. Yang, G. Luo and E. Y. Chang, "Flower-Like Distributed Self-Organized Ge Dots on Patterned Si (001) Substrates", Jap. J. Appl. Phys., Vol. 42, No. 6B, 2003, pp. L718-L720.
3. H. C. Chang, E. Y. Chang, Y. C. Lien, L. H. Chu, S. W. Chang, R. C. Huang and **H. M. Lee**, "Use of WN_x as Diffusion Barrier for Copper Airbridged Low Noise GaAs PHEMT", IEE Electron. Lett., Vol. 39, No. 24, 2003, pp. 1763-1765.
4. **H. M. Lee**, T. H. Yang, G. Luo and E. Y. Chang, "Controlled Placement of Self-Organized Ge Dots on Patterned Si (001) Surfaces", Jap. J. Appl. Phys., Vol. 43, No. 2B, 2004, pp. L247-L249.
5. Y. C. Lien, E. Y. Chang, H. C. Chang, L. H. Chu, G. W. Huang, **H. M. Lee**, C. S. Lee, S. H. Chen, P. T. Shen and C. Y. Chang, "Low Noise Metamorphic HEMTs with Reflowed 0.1 μm T-Gate", IEEE Electron. Device Lett., Vol. 25, No. 6, 2004, pp. 348-350.
6. E. Y. Chang, Y. C. Lin, G. J. Chen, **H. M. Lee**, G. W. Huang, D. Biswas and C. Y. Chang, "Composite-Channel Metamorphic High Electron Mobility Transistor for Low-Noise and High-Linearity Applications", Jap. J. Appl. Phys., Vol. 43, No. 7A, 2004, pp. L871-L872.
7. Y. C. Lin, E. Y. Chang, G. J. Chen, **H. M. Lee**, G. W. Huang, D. Biswas and C. Y. Chang, "InGaP/InGaAs PHEMT with High IP₃ for Low Noise Applications", IEE Electron. Lett., Vol. 40, No. 12, 2004, pp. 777-778.
8. **H. M. Lee**, K. Muraki, E. Y. Chang and Y. Hirayama, "Electronic Transport Characteristics in a One-Dimensional Constriction Defined by a Triple-Gate Structure", J. Appl. Phys., Vol. 100, 2006, pp. 043701.

B. 研討會論文

1. **H. M. Lee**, E. Y. Chang, S. H. Chen and S. C. Huang, 2003, May, "50-nm-T-gate fabricated by thermally reflowed resist technique", Symposium on Nano Device Technology 2003, pp. 5-8.
2. Y. C. Lien, E. Y. Chang, L. X. Chu, H. C. Chang, C. S. Lee, S. H. Chen; Y. C. Lin and **H. M. Lee**, 2003, September, "A metamorphic high electron-mobility transistor with reflowed submicron T-gate for high-speed optoelectronics applications", Proceedings of the Sixth Chinese Symposium, pp. 281-283.

3. Y. C. Lien, E. Y. Chang, H. C. Chang, L. H. Chu, K. W. Huang, **H. M. Lee**, C. S. Lee, S. H. Chen, P. T. Shen, 2003, October, “Low Noise Metamorphic HEMTs with reflowed submicron T-gate”, European Microwave 2003.
4. C. Y. Lu, K. S. Chen, **H. M. Lee**, E. Y. Chang, S. H. Chen, Y. C. Lin, G. J. Chen, 2003, November, “A low noise composite-channel metamorphic HEMT for wireless communication applications”, The IEEE Electron Devices for Microwave and Optoelectronic Applications, pp. 87-92.
5. Y. C. Lin, E. Y. Chang, G. J. Chen and **H. M. Lee**, 2003, December, “An InGaP/InGaAs PHEMT with High IP3 for Low Noise Application”, The 12th international workshop on the physics of semiconductor devices, pp. 845-847.
6. **H. M. Lee**, E. Y. Chang, Y. C. Lin, G. J. Chen, S. H. Chen, C. Y. Chang, 2003, December, “A Composite-channel Metamorphic HEMT with High Channel Breakdown Voltage for Power Applications”, The 12th international workshop on the physics of semiconductor devices, pp. 842-844.
7. L. H. Chu, E. Y. Chang, H. C. Chang, Y. C. Lien, S. W. Chang, R. C. Huang and **H. M. Lee**, 2004, May, “Copper Airbridged Low Noise GaAs PHEMT with WN_x as the Diffusion Barrier”, The International Conference on Compound Semiconductor Manufacturing Technology.

C. 專利

1. 利用熱回流光阻技術製造奈米級閘極於半導體裝置中之方法，張翼，李晃銘(台灣專利 194183，美國專利審查中)。